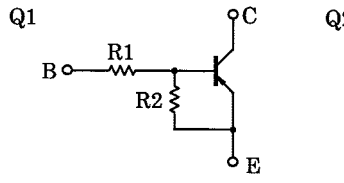
TOSHIBA Transistor
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

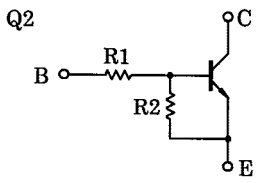
RN4606

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Including two devices in SM6 (super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

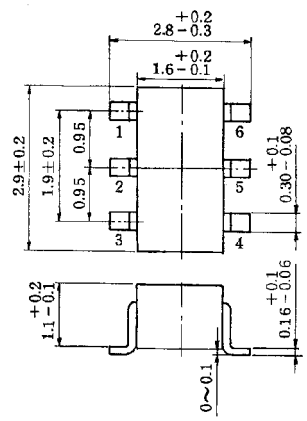
Equivalent Circuit and Bias Resister Values





R1: 4.7kΩ
R2: 47kΩ
(Q1, Q2 Common)

Unit in mm



1.	EMITTER 1 (E1)
2.	BASE 1 (B1)
3.	COLLECTOR 2 (C2)
4.	EMITTER 2 (E2)
5.	BASE 2 (B2)
6.	COLLECTOR 1 (C1)

SM6

JEDEC	—
EIAJ	—
TOSHIBA	2-3N1A

Weight: 0.015g

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−50	V
Collector-emitter voltage	V_{CEO}	−50	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA

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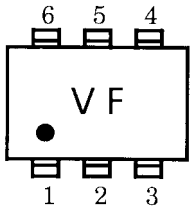
Q1, Q2 Common Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P_C *	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

* Total rating

Marking



Equivalent Circuit (Top View)